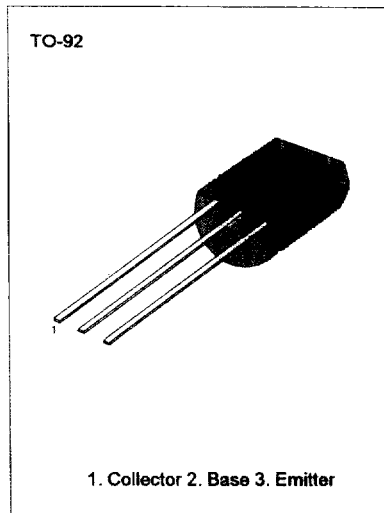


SWITCHING AND AMPLIFIER APPLICATIONS

- Suitable for AF-Driver stages and low power output stages
- Complement to BC337/BC328

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CE}		
:BC337		50	V
BC338		30	V
Collector-Emitter Voltage	V _{CEO}		
:BC337		45	V
BC338		25	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current (DC)	I _C	800	mA
Collector Dissipation	P _C	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ 150	°C



3

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C =10mA, I _B =0				
:BC337			45			V
:BC338			25			V
Collector Emitter Breakdown Voltage	BV _{CES}	I _C =0.1mA, I _B =0				
:BC337			50			V
:BC338			30			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E =0.1mA, I _C =0	-5			V
Collector Cut-off Current	I _{CES}					
:BC337		V _{CE} =45V, I _B =0		2	100	nA
:BC338		V _{CE} =25V, I _B =0		2	100	nA
DC Current Gain	h _{FE1} h _{FE2}	V _{CE} =1V, I _C =100mA V _{CE} =1V, I _C =300mA	100		630	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C =500mA, I _B =50mA			0.7	V
Base Emitter On Voltage	V _{BE (on)}	V _{CE} =1V, I _C =300mA			1.2	V
Current Gain Bandwidth Product	f _T	V _{CE} =5V, I _C =10mA		100		MHz
Collector Base Capacitance	C _{CB0}	V _{CB} =10V, f=1MHz		12		pF

h_{FE} CLASSIFICATION

Classification	16	26	40
h _{FE}	100-250	160-400	250-630
h _{FE2}	60-	100-	170-